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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: KANO, Takashi

APR 23 2003

Serial No.: 09/532,775

Group Art Unit: 2828

Filed: March 22, 2000

Examiner: Tuan M. Nguyen

P.T.O. Confirmation No.: 8757

For: SEMICONDUCTOR LASER DEVICE

SUPPLEMENTAL AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents  
Washington, D.C. 20231  
Sir:

April 23, 2003

In response to the Office Action dated April 10, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1-3 as indicated below:

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TECHNOLOGY CENTER 2800

1. (Amended) A semiconductor laser device comprising:

a first nitride based semiconductor layer including a first conductivity type cladding layer and an active layer and containing at least one of boron, aluminum, gallium, indium and thallium;  
*B1*  
a current blocking layer, formed on said first nitride based semiconductor layer, having a striped opening; and